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EXAMINER INITIAL	DOCUMENT NUMBER	IMBER DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
MITTAL				L		YES	NO
M	WO 00/38287	29.06.00	PCT				
n	WO 01/33677 A2	10.05.01	WIPO				
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M	H. Shimizu et al., 1.2 um range GalnAs S QW lasers using Sb as surfactant, ELECTRONICS LETTERS, Vol. 36, No. 16, August 3, 2000, 2 pages.
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EXAMINER HUMANDO PENINGUEZ DATE CONSIDERED 5-25-04						
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